



ELECTRONICS, INC.
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NTE373 (NPN) & NTE374 (PNP) Silicon Complementary Transistors Audio Amplifier, Driver

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector–Base Voltage, V_{CBO}	180V
Collector–Emitter Voltage, V_{CEO}	160V
Emitter–Base Voltage, V_{EBO}	5V
Collector Current, I_C	
Continuous	1.5A
Peak	3A
Collector Power Dissipation, P_D	
$T_A = +25^\circ\text{C}$	1W
$T_C = +25^\circ\text{C}$	20W
Operating Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	–55° to +150°C

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 1\text{mA}, I_E = 0$	180	–	–	V
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10\text{mA}, R_{BE} = \infty$	160	–	–	V
Emitter–Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 1\text{mA}, I_C = 0$	5	–	–	V
Collector Cutoff Current	I_{CBO}	$V_{CB} = 160\text{V}, I_E = 0$	–	–	10	μA
DC Current Gain	h_{FE1}	$V_{CE} = 5\text{V}, I_C = 150\text{mA}$	60	–	200	
	h_{FE2}	$V_{CE} = 5\text{V}, I_C = 500\text{mA}$	30	–	–	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$	–	–	1	V
Base–Emitter Voltage	V_{BE}	$V_{CE} = 5\text{V}, I_C = 150\text{mA}$	–	–	1.5	V
Transistion Frequency	f_T	$V_{CE} = 5\text{V}, I_C = 500\text{mA}$	–	140	–	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$	–	14	–	pF

